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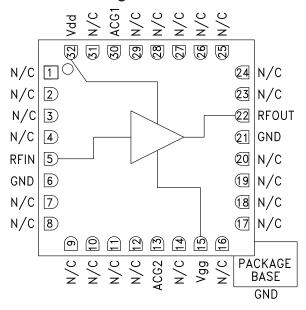
## GaAs pHEMT MMIC LOW NOISE AMPLIFIER, DC - 20 GHz

#### Typical Applications

The HMC460LC5 is ideal for:

- Telecom Infrastructure
- Microwave Radio & VSAT
- Military & Space
- Test Instrumentation

#### **Functional Diagram**



#### **Features**

Noise Figure: 2.5 dB @ 10 GHz

Gain: 14 dB @ 10 GHz

P1dB Output Power: +16.5 dBm @ 10 GHz

Supply Voltage: +8V @ 75 mA 50 Ohm Matched Input/Output

32 Lead Ceramic 5 x 5 mm SMT Package: 25 mm<sup>2</sup>

#### **General Description**

The HMC460LC5 is a GaAs MMIC pHEMT Low Noise Distributed Amplifier in a leadless 5 x 5 mm ceramic surface mount package which operates from DC to 20 GHz. The amplifier provides 14 dB of gain, 2.5 dB noise figure and +16.5 dBm of output power at 1 dB gain compression while requiring only 75 mA from a Vdd = 8V supply. Gain flatness is excellent from DC to 20 GHz making the HMC460LC5 ideal for EW, ECM, Radar and test equipment applications. The wideband amplifier I/Os are internally matched to 50 Ohms.

## Electrical Specifications, $T_{\Delta} = +25$ °C, Vdd= 8V, Idd= 75 mA\*

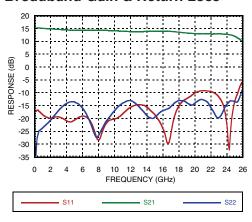
Parameter	Min.	Тур.	Max.	Min.	Тур.	Max.	Min.	Тур.	Max.	Units
Frequency Range	DC - 6.0		6.0 - 18.0		18.0 - 20.0		GHz			
Gain	11	14		11	14		10	13		dB
Gain Flatness		± 0.5			± 0.15			± 0.25		dB
Gain Variation Over Temperature		0.008			0.01			0.01		dB/ °C
Noise Figure		3.5	5.0		2.5	4.0		3.5	5	dB
Input Return Loss		17			18			12		dB
Output Return Loss		17			15			15		dB
Output Power for 1 dB Compression (P1dB)	14	17		13	16		12	15		dBm
Saturated Output Power (Psat)		18			18			17		dBm
Output Third Order Intercept (IP3)		29.5			29			28.5		dBm
Supply Current (Idd) (Vdd= 8V, Vgg= -0.9V Typ.)		75			75			75		mA

\*Adjust Vgg between -2 to 0V to achieve Idd= 75 mA typical.

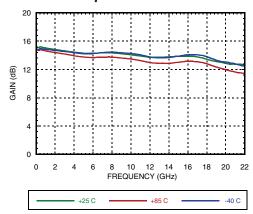


## GaAs pHEMT MMIC LOW NOISE AMPLIFIER, DC - 20 GHz

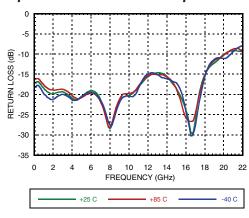
#### **Broadband Gain & Return Loss**



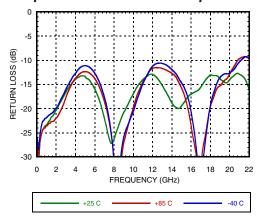
#### Gain vs. Temperature



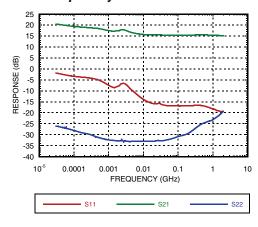
#### Input Return Loss vs. Temperature



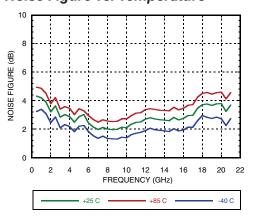
Output Return Loss vs. Temperature



#### Low Frequency Gain & Return Loss



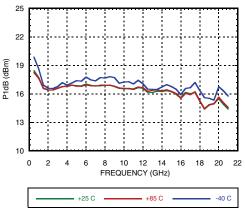
*Noise Figure vs. Temperature* 

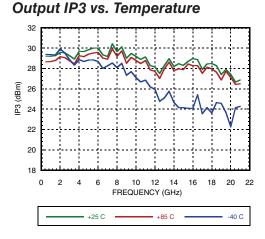




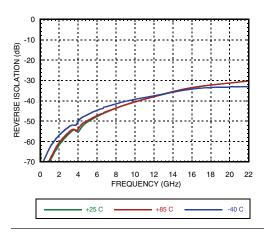
## GaAs pHEMT MMIC LOW NOISE AMPLIFIER, DC - 20 GHz

# P1dB vs. Temperature

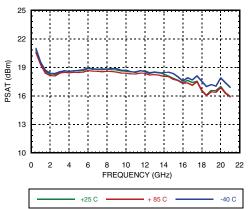




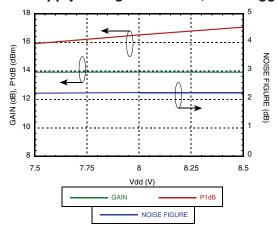
#### Reverse Isolation vs. Temperature



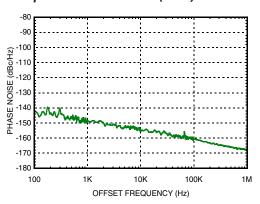
#### Psat vs. Temperature



Gain, Power & Noise Figure vs. Supply Voltage @ 10 GHz, Fixed Vgg



Additive Phase Noise Vs Offset Frequency, RF Frequency = 10 GHz, RF Input Power = 8 dBm (Psat)





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## GaAs pHEMT MMIC LOW NOISE AMPLIFIER, DC - 20 GHz

#### **Absolute Maximum Ratings**

Drain Bias Voltage (Vdd)	+9 Vdc
Gate Bias Voltage (Vgg)	-2 to 0 Vdc
Gate Bias Voltage (Igg)	2.5 mA
RF Input Power (RFIN)(Vdd = +8 Vdc)	+18 dBm
Channel Temperature	175 °C
Continuous Pdiss (T = 85 °C) (derate 23 mW/°C above 85 °C)	2 W
Thermal Resistance (channel to package bottom)	44.4 °C/W
Storage Temperature	-65 to +150 °C
Operating Temperature	-55 to +85 °C
ESD Sensitivity (HBM)	Class 1A

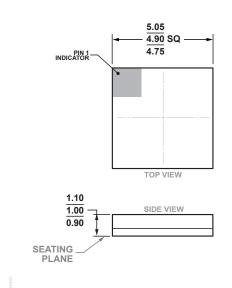
#### Typical Supply Current vs. Vdd

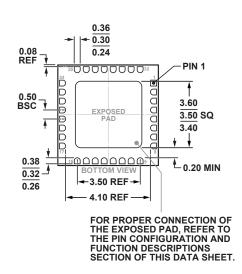
Vdd (V)	Idd (mA)
+7.5	74
+8.0	75
+8.5	76



ELECTROSTATIC SENSITIVE DEVICE OBSERVE HANDLING PRECAUTIONS

### **Outline Drawing**





32-Terminal Ceramic Leadless Chip Carrier [LCC]
(E-32-1)
Dimensions shown in millimeters.

#### **ORDERING GUIDE**

Part Number	Package Material	Lead Finish	MSL Rating	Package Marking [2]
HMC460LC5	Alumina, White	Gold over Nickel	MSL3 [1]	H460 XXXX

[1] Max peak reflow temperature of 260 °C

[2] 4-Digit lot number XXXX



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## GaAs pHEMT MMIC LOW NOISE AMPLIFIER, DC - 20 GHz

## **Pin Descriptions**

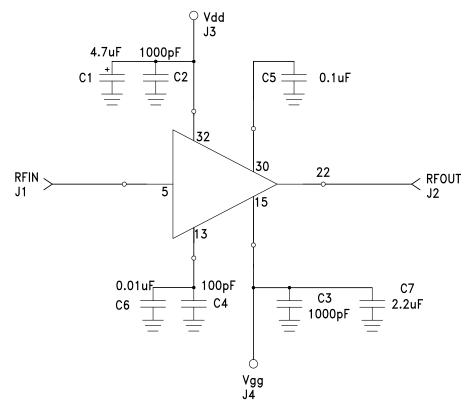
Pin Number	Function	Description	Interface Schematic
1 - 4, 7 - 12, 14, 16 - 20, 23 - 29, 31	N/C	No connection. These pins may be connected to RF ground.  Performance will not be affected.	
5	RFIN	This pin is DC coupled and matched to 50 Ohms.	RFIN ACG2
6, 21	GND	Package bottom must be connected to RF/DC ground.	○ GND =
13	ACG2	Low frequency termination. Attach bypass capacitor per application circuit herein.	RFIN ACG2
15	Vgg	Gate control for amplifier. Please follow "MMIC Amplifier Biasing Procedure" application note	Vgg O
22	RFOUT	This pin is DC coupled and matched to 50 Ohms.	○ RFOUT
30	ACG1	Low frequency termination. Attach bypass capacitor per application circuit herein.	ACG1 RFOUT
32	Vdd	Power supply voltage for the amplifier. External bypass capacitors are required	OVdd



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## GaAs pHEMT MMIC LOW NOISE AMPLIFIER, DC - 20 GHz

## **Application Circuit**

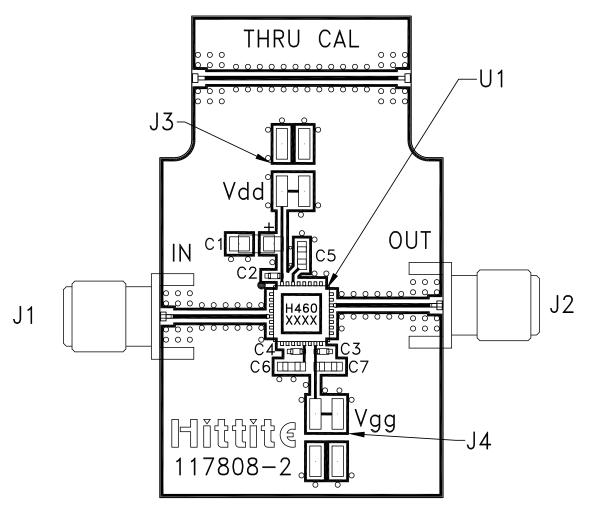




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## GaAs pHEMT MMIC LOW NOISE AMPLIFIER, DC - 20 GHz

#### **Evaluation PCB**



#### List of Materials for Evaluation PCB 117810 [1]

Item	Description	
J1 - J2	PCB Mount SMA Connector	
J3 - J4	2 mm Molex Header	
C4	100 pF Capacitor, 0402 Pkg.	
C2, C3	1000 pF Capacitor, 0402 Pkg.	
C1	4.7 μF Capacitor, Tantalum	
C5	0.1 uF Capacitor, 0603 Pkg.	
C6	0.01 uF Capacitor, 0603 Pkg.	
C7	2.2 uF Capacitor, 0603 Pkg.	
U1	HMC460LC5	
PCB [2]	117808 Evaluation PCB	

<sup>[1]</sup> Reference this number when ordering complete evaluation PCB

The circuit board used in the application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and package bottom should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation board should be mounted to an appropriate heat sink. The evaluation circuit board shown is available from Analog Devices upon request.

<sup>[2]</sup> Circuit Board Material: Rogers 4350

# **Mouser Electronics**

**Authorized Distributor** 

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Analog Devices Inc.:

HMC460LC5TR HMC460LC5 117810-HMC460LC5 HMC460LC5TR-R5